

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT(S): Shen et al. CONF. NO.: 1665
SERIAL NO.: 10/582,035 GROUP NO.: 4146
FILING DATE: May 7, 2007 EXAMINER: Huber, Robert T.
TITLE: MONOLITHIC POWER SEMICONDUCTOR STRUCTURES

Mail Stop Amendment
Commissioner for Patents
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AMENDMENT AND RESPONSE

This paper responds to the Office Action mailed on February 25, 2008, in the above-identified patent application.

Please amend the above-identified patent application as follows, without prejudice:

- **Amendments to the specification** begins on page 2 of this paper;
- **Listing of claims** begins on page 3 of this paper; and
- **Remarks** begin on page 9 of this paper.

Amendments to the Specification

Please amend the title as follows:

Monolithic Power Semiconductor Structures Including Pairs of Integrated Devices

Please re-write paragraph [0029] as indicated below:

[0029] FIG. 9 depicts a second~~seventh~~ aspect of the present invention in accordance with the teachings presented herein.

Please re-write the Abstract as indicated below:

Provided herein are exemplary embodiments of m~~Monolithic~~ semiconductor structures having at least two pairs of two lateral e~~n~~onstructed-semiconductor devices combined on a first surface of a single semiconductor substrate. Embodiments include connected source terminals defining common source terminals.